

18. (Twice Amended) A method of manufacturing a semiconductor device, which comprises:

forming a wiring groove on a surface of an insulating film formed above a semiconductor substrate;

depositing a conductive material film on a surface of said insulating film including an inner surface of said wiring groove; and

subjecting said conductive material film to a chemical mechanical polishing by making use of a slurry for chemical mechanical polishing, which contains polishing particles comprising first colloidal silica particles whose primary particles have a diameter ranging from 5 to 20 nm, and second colloidal silica particles whose primary particles have a diameter ranging from 20 nm to 50 nm, wherein the weight ratio of the first colloidal silica particles is in the range of 0.6 to 0.9 based on a total weight of said first and second colloidal silica particles to remove said conductive material film excluding a conductive material film portion which is buried in said wiring groove.

23. (Twice Amended) A method of manufacturing a semiconductor device, which comprises:

forming a wiring groove on a surface of an insulating film formed above a semiconductor substrate;

depositing a conductive barrier film on a surface of said insulating film including an inner surface of said wiring groove;

depositing a wiring material film on said conductive barrier film to fill said wiring groove with said wiring material film;

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